

# Jeong Hyun Moon

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

35  
papers

395  
citations

8  
h-index

19  
g-index

48  
ext. papers

439  
ext. citations

1.7  
avg, IF

2.8  
L-index

#	Paper	IF	Citations
35	Double p-base structure for 1.2-kV SiC trench MOSFETs with the suppression of electric-field crowding at gate oxide. <i>Microelectronic Engineering</i> , <b>2020</b> , 225, 111280	2.5	2
34	TEOS-based low-pressure chemical vapor deposition for gate oxides in 4H-SiC MOSFETs using nitric oxide post-deposition annealing. <i>Current Applied Physics</i> , <b>2020</b> , 20, 1386-1390	2.6	3
33	Ultra-Wide Bandgap $\text{AlGaO}_3$ Heterojunction Field-Effect Transistor Using p-Type 4H-SiC Gate for Efficient Thermal Management. <i>ECS Journal of Solid State Science and Technology</i> , <b>2020</b> , 9, 065006	2	3
32	Effect of sweeping direction on the capacitance-voltage behavior of sputtered $\text{SiO}_2$ /4H-SiC metal-oxide semiconductors after nitric oxide post-deposition annealing. <i>Physica Scripta</i> , <b>2019</b> , 94, 125816	2.6	3
31	High-voltage LDIMOSFETs on HPSI 4H-SiC substrate with dual field plates. <i>Physica Scripta</i> , <b>2019</b> , 94, 105809	2.6	1
30	High-voltage lateral double-implanted MOSFETs implemented on high-purity semi-insulating 4H-SiC substrates with gate field plates. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 06HC08	1.4	4
29	Formation of the Uniform Interface Ni/4H-SiC Ohmic Contact with Titanium as Barrier Layer. <i>Materials Science Forum</i> , <b>2018</b> , 924, 397-400	0.4	1
28	Fabrication of 4H-SiC lateral double implanted MOSFET on an on-axis semi-insulating substrate without using epi-layer. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 120305	1.4	8
27	Oxygen- and photoresist-related interface states of 4H-SiC Schottky diode observed by deep-level transient spectroscopy. <i>Journal of Applied Physics</i> , <b>2017</b> , 122, 094504	2.5	2
26	Effect of surface passivation on breakdown voltages of 4H-SiC Schottky barrier diodes. <i>Journal of the Korean Physical Society</i> , <b>2017</b> , 71, 707-710	0.6	2
25	Fabrication of a 1.7-kV Schottky barrier diode with improved forward current-voltage characteristics. <i>Journal of the Korean Physical Society</i> , <b>2016</b> , 68, 810-814	0.6	1
24	Role of the oxidizing agent in the etching of 4H-SiC substrates with molten KOH. <i>Journal of the Korean Physical Society</i> , <b>2016</b> , 69, 1677-1682	0.6	1
23	Impact of Stacking Fault on the I-V Characteristics of 4H-SiC Schottky Barrier Diode. <i>Materials Science Forum</i> , <b>2015</b> , 821-823, 563-566	0.4	2
22	Investigation of $\text{SiO}_2$ film growth on 4H-SiC by direct thermal oxidation and postoxidation annealing techniques in $\text{HNO}_3$ & $\text{H}_2\text{O}$ vapor at varied process durations. <i>Thin Solid Films</i> , <b>2014</b> , 570, 138-149	2.2	3
21	Improved 4H-SiC metal oxide semiconductor interface produced by using an oxidized SiN gate oxide that had undergone post-oxidation annealing. <i>Journal of the Korean Physical Society</i> , <b>2014</b> , 64, 1363-1369	0.6	3
20	Investigation of thermally grown oxide on 4H-SiC by a combination of $\text{H}_2\text{O}$ and $\text{HNO}_3$ vapor with varied $\text{HNO}_3$ solution heating temperature. <i>Applied Surface Science</i> , <b>2013</b> , 285, 795-804	6.7	5
19	Crystal splitting and enhanced photocatalytic behavior of $\text{TiO}_2$ rutile nano-belts induced by dislocations. <i>Nanoscale</i> , <b>2013</b> , 5, 753-8	7.7	44

18	Effects of wet-oxidized 4H-SiC annealed in HNO <sub>3</sub> /H <sub>2</sub> O vapour. <i>Microelectronics International</i> , <b>2013</b> , 31, 42-53	0.8	2
17	Effects of post-oxidation annealing temperature on ZrO <sub>2</sub> thin film deposited on 4H-SiC substrate. <i>Materials Science in Semiconductor Processing</i> , <b>2011</b> , 14, 13-17	4.3	22
16	Improved 4H-SiC MOS Interface Produced by Oxidized-SiN Gate Oxide. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 511-514	0.4	2
15	Effects of rapid thermal annealing on Al <sub>2</sub> O <sub>3</sub> /SiN reaction barrier layer/thermal-nitrided SiO <sub>2</sub> stacking gate dielectrics on n-type 4H-SiC. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 122108	3.4	6
14	Effect of Postoxidation Annealing on High Temperature Grown SiO <sub>2</sub> /4H-SiC Interfaces. <i>Journal of the Electrochemical Society</i> , <b>2010</b> , 157, H196	3.9	11
13	Observation of stacking faults formed during homoepitaxial growth of p-type 4H-SiC. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 112109	3.4	3
12	Current conduction mechanisms in atomic-layer-deposited HfO <sub>2</sub> /nitrided SiO <sub>2</sub> stacked gate on 4H silicon carbide. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 084113	2.5	110
11	Homoepitaxial Growth of Vanadium-Doped Semi-insulating 4H-SiC Using Bis-trimethylsilylmethane and Bis-cyclopentadienylvanadium Precursors. <i>Journal of the Electrochemical Society</i> , <b>2008</b> , 155, H11	3.9	6
10	Effects of heat treatment in vacuum on the physical properties of thermal nitrided silicon dioxide gate on 4H-silicon carbide. <i>Thin Solid Films</i> , <b>2008</b> , 516, 7921-7924	2.2	1
9	Heavily nitrogen-doped 4H-SiC homoepitaxial films grown on porous SiC substrates. <i>Journal of Crystal Growth</i> , <b>2007</b> , 305, 83-87	1.6	6
8	Electronic Properties of Atomic-Layer-Deposited Al <sub>2</sub> O <sub>3</sub> /Thermal-Nitrided SiO <sub>2</sub> Stacking Dielectric on 4H SiC. <i>Electrochemical and Solid-State Letters</i> , <b>2007</b> , 10, H69		32
7	Analysis of current conduction mechanisms in atomic-layer-deposited Al <sub>2</sub> O <sub>3</sub> gate on 4H silicon carbide. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 162113	3.4	33
6	Homoepitaxial Growth of Vanadium-Doped 4H-SiC Using Bis-Trimethylsilylmethane and Verrocene Precursors. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 113-116	0.4	
5	Electrical Properties of Atomic-Layer-Deposited La <sub>2</sub> O <sub>3</sub> /Thermal-Nitrided SiO <sub>2</sub> Stacking Dielectric on 4H-SiC(0001). <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 643-646	0.4	8
4	4H-SiC Planar MESFETs on High-Purity Semi-Insulating Substrates. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 763-766	0.4	5
3	Electrical Properties of Metal-Oxide-Semiconductor (MOS) Structures on 4H-SiC(0001) Formed by Oxidizing Pre-Deposited SixNy. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 647-650	0.4	1
2	Homoepitaxial growth and electrical characterization of iron-doped semi-insulating 4H-SiC epilayer. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 152112	3.4	18
1	Fabrication and characterization of 4H-SiC planar MESFETs. <i>Microelectronic Engineering</i> , <b>2006</b> , 83, 160-164	5	40

